INCH-POUND MIL-M-38510/372B

27 July 2004 SUPERSEDING MIL-M-38510/372A 12 February 1987

#### MILITARY SPECIFICATION

# MICROCIRCUITS, DIGITAL, BIPOLAR, ADVANCED LOW POWER SCHOTTKY TTL, FLIP-FLOPS CASCADABLE, MONOLITHIC SILICON

Inactive for new design after 8 July 1997.

This specification is approved for use by all Departments and Agencies of the Department of Defense.

The requirements for acquiring the product herein shall consist of this specification sheet and MIL-PRF 38535

- 1. SCOPE
- 1.1 <u>Scope</u>. This specification covers the detail requirements for monolithic silicon, advanced low power Schottky TTL, flip-flops, bistable logic microcircuits. Two product assurance classes and a choice of case outlines and lead finishes are provided for each type and are reflected in the complete part number. For this product, the requirements of MIL-M-38510 have been superseded by MIL-PRF-38535, (see 6.3).
  - 1.2 Part or Identifying Number (PIN). The PIN is in accordance with MIL-PRF-38535, and as specified herein.
  - 1.2.1 <u>Device types.</u> The device types are as follows:

Device type	<u>Circuit</u>
01	Hex D-type flip-flop with clear cascadable
02	Quadruple D-type flip-flop with clear cascadable
03	Octal D-type flip-flop with transparent latch and
	3 state outputs cascadable
04	Octal D-type flip-flop with 3 state outputs cascadable

- 1.2.2 <u>Device class</u>. The device class is the product assurance level as defined in MIL-PRF-38535.
- 1.2.3 Case outlines. The case outlines are as designated in MIL-STD-1835 and as follows:

Outline letter	<u>Descriptive designator</u>	<u>Terminals</u>	Package style
E	GDIP1-T16 or CDIP2-T16	16	Dual-in-line
F	GDFP2-F16 or CDFP3-F16	16	Flat pack
R	GDIP1-T20 or CDIP2-T20	20	Dual-in-line
S	GDFP2-F20 or CDFP3-F20	20	Flat pack
2	CQCC1-N20	20	Square leadless chip carrier

Comments, suggestions, or questions on this document should be addressed to: Commander, Defense Supply Center Columbus, ATTN: DSCC-VAS, P. O. Box 3990, Columbus, OH 43218-3990, or emailed to bipolar@dscc.dla.mil. Since contact information can change, you may want to verify the currency of this address information using the ASSIST Online database at www.dodssp.daps.mil.

AMSC N/A FSC 5962

# 1.3 Absolute maximum ratings.

Supply voltage range	-0.5 V dc to +7.0 V dc
Input voltage range	-1.5 V dc at -18 mA to +7.0 V dc
Storage temperature range	-65° to +150°C
Maximum power dissipation (P <sub>D</sub> ), per device: 1/	
Device 01	104.5 mW
Device 02	
Device 03	148.5 mW
Device 04	
Lead temperature (soldering, 10 seconds)	+300°C
Thermal resistance, junction to case ( $\theta_{JC}$ ):	
Cases E, F, R, S, and 2	(See MIL-STD-1835)
Junction temperature (T <sub>J</sub> ) <u>2</u> /	
• • • • • • • • • • • • • • • • • • •	
1.4 Recommended operating conditions.	
Supply voltage (V <sub>CC</sub> )	
	maximum
Minimum high level input voltage (V <sub>IH</sub> )	
Maximum low level input voltage (V <sub>IL</sub> )	
Normalized fanout (each output) 3/	
	20 maximum at high logic level
Case operating temperature range (T <sub>C</sub> )	-55° to +125°C
Minimum width of clock pulse (t <sub>P(CLK)</sub> )	
type 01, 02 25°C	
-55/125°C	12.5 ns
type 04 25°C	14 ns
-55/125°C	16.5 ns
Minimum width of clear pulse (t <sub>P(CLEAR)</sub> )	
type 01, 02	15 ns
Minimum width of enable pulse (tP(ENABLE))	
type 03	10 ns
Minimum setup time before clock (tsetup)	
type 01, 02	16 ns
type 04	10 ns
Minimum hold time after clock (t <sub>HOLD</sub> )	
type 01, 02	
type 04	4 ns
Minimum setup time before enable (tsetup)	
type 03	10 ns
Minimum hold time after enable (t <sub>HOLD</sub> )	_
type 03	7 ns
Minimum clear inactive state time before clock	
type 01, 02	8 ns

Must withstand the added P<sub>D</sub> due to short-circuit test (e.g., I<sub>OS</sub>).
 Maximum junction temperature should not be exceeded except in accordance with allowable short duration burn-in screening condition in accordance with MIL-PRF-38535.

<sup>3/</sup> The device should fanout in both high and low levels to the specified number of inputs of the same device type as that being tested.

## 2. APPLICABLE DOCUMENTS

2.1 <u>General.</u> The documents listed in this section are specified in sections 3, 4, or 5 of this specification. This section does not include documents cited in other sections of this specification or recommended for additional information or as examples. While every effort has been made to ensure the completeness of this list, document users are cautioned that they must meet all specified requirements of documents cited in sections 3, 4, or 5 of this specification, whether or not they are listed.

## 2.2 Government documents.

2.2.1 <u>Specifications and standards.</u> The following specifications and standards form a part of this specification to the extent specified herein. Unless otherwise specified, the issues of these documents are those cited in the solicitation or contract.

#### DEPARTMENT OF DEFENSE SPECIFICATIONS

MIL-PRF-38535 - Integrated Circuits (Microcircuits) Manufacturing, General Specification for.

## DEPARTMENT OF DEFENSE STANDARDS

MIL-STD-883 - Test Method Standard for Microelectronics.

MIL-STD-1835 - Interface Standard Electronic Component Case Outlines

(Copies of these documents are available online at http://assist.daps.dla.mil/quicksearch/ or www.dodssp.daps.mil or from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

2.3 <u>Order of precedence.</u> In the event of a conflict between the text of this specification and the references cited herein, the text of this document takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

#### 3. REQUIREMENTS

- 3.1 <u>Qualification</u>. Microcircuits furnished under this specification shall be products that are manufactured by a manufacturer authorized by the qualifying activity for listing on the applicable qualified manufacturers list before contract award (see 4.3 and 6.4).
- 3.2 <u>Item requirements</u>. The individual item requirements shall be in accordance with MIL-PRF-38535 and as specified herein or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein.
- 3.3 <u>Design, construction, and physical dimensions.</u> The design, construction, and physical dimensions shall be as specified in MIL-PRF-38535 and herein.
  - 3.3.1 Case outlines. The case outlines shall be as specified in 1.2.3.
  - 3.3.2 <u>Terminal connections.</u> The terminal connections shall be as specified on figure 1.
  - 3.3.3 <u>Logic equations.</u> The logic equations shall be as specified on figure 2.
  - 3.3.4 Truth tables. The truth tables shall be as specified on figure 3.

- 3.3.5 <u>Schematic circuits</u>. The schematic circuits shall be maintained by the manufacturer and made available to the qualifying activity and the preparing activity upon request.
  - 3.4 Lead material and finish. The lead material and finish shall be in accordance with MIL-PRF-38535 (see 6.6).
- 3.5 <u>Electrical performance characteristics</u>. The electrical performance characteristics are as specified in table I, and apply over the full recommended case operating temperature range, unless otherwise specified.
- 3.6 <u>Electrical test requirements</u>. The electrical test requirements for each device class shall be the subgroups specified in table II. The electrical tests for each subgroup are described in table III.
  - 3.7 Marking. Marking shall be in accordance with MIL-PRF-38535.
- 3.8 <u>Microcircuit group assignment.</u> The devices covered by this specification shall be in microcircuit group number 10 (see MIL-PRF-38535, appendix A).

#### 4. VERIFICATION

- 4.1 <u>Sampling and inspection.</u> Sampling and inspection procedures shall be in accordance with MIL-PRF-38535 or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not effect the form, fit, or function as described herein.
- 4.2 <u>Screening.</u> Screening shall be in accordance with MIL-PRF-38535 and shall be conducted on all devices prior to qualification and conformance inspection. The following additional criteria shall apply:
  - a. The burn-in test duration, test condition, and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document control by the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015 of MIL-STD-883.
  - b. Interim and final electrical test parameters shall be as specified in table II, except interim electrical parameters test prior to burn-in is optional at the discretion of the manufacturer.
  - c. Additional screening for space level product shall be as specified in MIL-PRF-38535.

TABLE I. <u>Electrical performance characteristics</u>.

Test	Symbol	Con	ditions	Device	Lin	nits	Unit
		-55°C ≤ T	c ≤ +125°C	type	Min	Max	
		unless other	wise specified				
High level output voltage	V <sub>OH</sub>	$V_{CC} = 4.5 \text{ V},$	I <sub>OH</sub> = -400 μA	01, 02	2.5		V
		$V_{IH} = 2.0 V,$	I <sub>OH</sub> = -1.0 mA	03, 04	2.4		
		$V_{IL} = 0.8 \text{ V}$					
Low level output voltage	V <sub>OL</sub>	V <sub>CC</sub> = 4.5 V,	I <sub>OL</sub> = 4 mA	01, 02		0.4	V
		$V_{IH} = 2.0 V,$	I <sub>OL</sub> = 12 mA	03, 04		0.4	
		V <sub>IL</sub> = 0.8 V					
Input clamp voltage	V <sub>IC</sub>	$V_{CC} = 4.5 \text{ V}, I_{OL}$	= -18 mA,	All		-1.5	V
		T <sub>C</sub> = +25°C					
Low level input current	I <sub>IL</sub>	$V_{CC} = 5.5 \text{ V},$	D-inputs	01, 02	0	-100	μΑ
		$V_{IN} = 0.4 \text{ V}$	CLK/CLR		0	-150	
				03, 04	0	-200	
High level input current	I <sub>IH1</sub>	V <sub>CC</sub> = 5.5 V, V <sub>I</sub>	<sub>V</sub> = 2.7 V	All		20	μΑ
							•
	I <sub>IH2</sub>	V <sub>CC</sub> = 5.5 V, V <sub>IN</sub>	<sub>V</sub> = 7.0 V	All		100	μА
							•
Output current, low level,	I <sub>OZL</sub>	$V_{CC} = 5.5 \text{ V},$		03, 04		-20	μΑ
outputs disabled		V <sub>O</sub> = 0.4 V					•
Output current, high level,	I <sub>OZH</sub>	$V_{CC} = 5.5 \text{ V},$		03, 04		20	μΑ
outputs disabled		V <sub>O</sub> = 2.7 V					•
Short circuit output current	Io		out = 2.25 V <u>1</u> /	All	-20	-112	mA
'		, ,	_				
Supply current	Icc	V <sub>CC</sub> = 5.5 V, V <sub>I</sub>	<sub>N</sub> = 4.5 V <u>2</u> /	01		19	mA
				02		14	
Supply current outputs	I <sub>CCH</sub>	V <sub>CC</sub> = 5.5 V, V <sub>I</sub>	<sub>N</sub> = 4.5 V	03		16	mA
high				04		19	
Supply current outputs	I <sub>CCL</sub>	V <sub>CC</sub> = 5.5 V, V <sub>IN</sub>	ν = 0 V	03		25	mA
low				04		28	
Supply current outputs	I <sub>CCZ</sub>	V <sub>CC</sub> = 5.5 V		03		27	mA
disabled				04		31	
Maximum clock frequency	f <sub>MAX</sub>			01, 02	40		MHz
				04	30		

See footnotes at end of table.

TABLE I. Electrical performance characteristics.

Test	Symbol	Conditions	Device	Lin	nits	Unit
		-55°C ≤ T <sub>C</sub> ≤ +125°C	type	Min	Max	
		unless otherwise specified				
Propagation delay time,	t <sub>PLH1</sub>	$V_{CC} = 5.0 \text{ V}, C_L = 50 \text{ pF} \pm 10\%,$	01	3	18	ns
low-to-high, CLK to Q		$R_L = R1 = 500 \Omega$	02	3	17	
			04	4	20	
Propagation delay time,	t <sub>PHL1</sub>		01	5	20	ns
high-to-low, CLK to Q			02	5	26	
			04	5	18	
Propagation delay time,	t <sub>PLH2</sub>		03	2	14	ns
low-to-high, D to Q						
Propagation delay time,	t <sub>PHL2</sub>		03	4	19	ns
high-to-low, D to Q						
Propagation delay time,	t <sub>PLH3</sub>		03	6	21	ns
low-to-high, ENC to Q						
Propagation delay time,	t <sub>PHL3</sub>		03	7	21	ns
high-to-low, ENC to Q						
Propagation delay time,	t <sub>PLH4</sub>		02	5	20	ns
low-to-high, Clear to Q						
Propagation delay time,	t <sub>PHL4</sub>		01, 02	8	26	ns
high-to-low, Clear to Q						
Propagation delay time,	t <sub>PZH</sub>		03	5	26	ns
disable to high level			04	3	22	
Propagation delay time,	t <sub>PZL</sub>		03	6	22	ns
disable to low level			04	5	20	
Propagation delay time,	t <sub>PHZ</sub>		03	2	12	ns
high level to disable			04	1	12	
Propagation delay time,	$t_{PLZ}$		03	2	18	ns
low level to disable			04	2	24	

 $<sup>\</sup>underline{1}$ / The output conditions have been chosen to produce a current that closely approximates one half of the true short-circuit output current,  $I_{OS}$ .

 $<sup>\</sup>underline{2}\!/\ I_{\text{CC}}$  is measured with D inputs and  $\overline{\text{CLR}}\$  grounded.

TABLE II. Electrical test requirements.

	Subgroups	(see table III)
MIL-PRF-38535	Class S	Class B
test requirements	devices	devices
Interim electrical parameters	1	1
Final electrical test parameters	1*, 2, 3, 7, 9, 10, 11	1*, 2, 3, 7, 9
Group A test requirements	1, 2, 3, 7, 8, 9, 10, 11	1, 2, 3, 7, 8, 9, 10, 11
Group B electrical test parameters when using the method 5005 QCI option	1, 2, 3, 9, 10, 11	N/A
Group C end-point electrical parameters	1, 2, 3, 9, 10, 11	1, 2, 3
Group D end-point electrical parameters	1, 2, 3	1, 2, 3

<sup>\*</sup>PDA applies to subgroup 1.

- 4.3 Qualification inspection. Qualification inspection shall be in accordance with MIL-PRF-38535.
- 4.4 <u>Technology Conformance Inspection (TCI)</u>. Technology conformance inspection shall be in accordance with MIL-PRF-38535 and herein for groups A, B, C, and D inspections (see 4.4.1 through 4.4.4).
- 4.4.1 <u>Group A inspection.</u> Group A inspection shall be in accordance with table III of MIL-PRF-38535 and as follows:
  - a. Tests shall be as specified in table II herein.
  - b. Subgroups 4, 5, and 6 shall be omitted.
  - 4.4.2 Group B inspection. Group B inspection shall be in accordance with table II of MIL-PRF-38535.
- 4.4.3 Group C inspection. Group C inspection shall be in accordance with table IV of MIL-PRF-38535 and as follows:
  - a. End-point electrical parameters shall be as specified in table II herein.
  - b. The steady-state life test duration, test condition, and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document control by the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005 of MIL-STD-883.
- 4.4.4 <u>Group D inspection.</u> Group D inspection shall be in accordance with table V of MIL-PRF-38535. End-point electrical parameters shall be as specified in table II herein.
  - 4.5 Methods of inspection. Methods of inspection shall be specified as follows:
- 4.5.1 <u>Voltage and current.</u> All voltages given are referenced to the microcircuit ground terminal. Currents given are conventional and positive when flowing into the referenced terminal.

	Devi	ce 01	Devic	e 02	Device 03	Device 04
Terminal	Cases	Case	Cases	Cases	Cases	Cases
number	E and F	2	E and F	2	R, S, and 2	R, S, and 2
1	CLR	N/C	CLR	N/C	OC	<del>OC</del>
2	1Q	CLR	1Q	CLR	1Q	1Q
3	1D	1Q	1 Q	1Q	1D	1D
4	2D	1D	1D	1 Q	2D	2D
5	2Q	2D	2D	1D	2Q	2Q
6	3D	N/C	2Q	N/C	3Q	3Q
7	3Q	2Q	2Q	2D	3D	3D
8	GND	3D	GND	2 \( \overline{Q} \)	4D	4D
9	CLK	3Q	CLK	2Q	4Q	4Q
10	4Q	GND	3Q	GND	GND	GND
11	4D	N/C	3 \( \overline{Q} \)	N/C	ENC	CLK
12	5Q	CLK	3D	CLK	5Q	5Q
13	5D	4Q	4D	3Q	5D	5D
14	6D	4D	4 Q	3 Q	6D	6D
15	6Q	5Q	4Q	3D	6Q	6Q
16	$V_{CC}$	N/C	V <sub>CC</sub>	N/C	7Q	7Q
17		5D		4D	7D	7D
18		6D		4 Q	8D	8D
19		6Q		4Q	8Q	8Q
20		Vcc		Vcc	V <sub>CC</sub>	Vcc

FIGURE 1. <u>Terminal connections</u>.

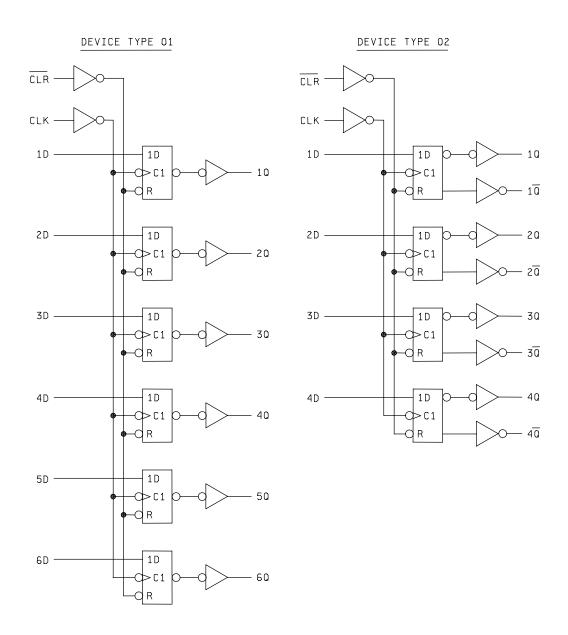


FIGURE 2. Logic diagrams.

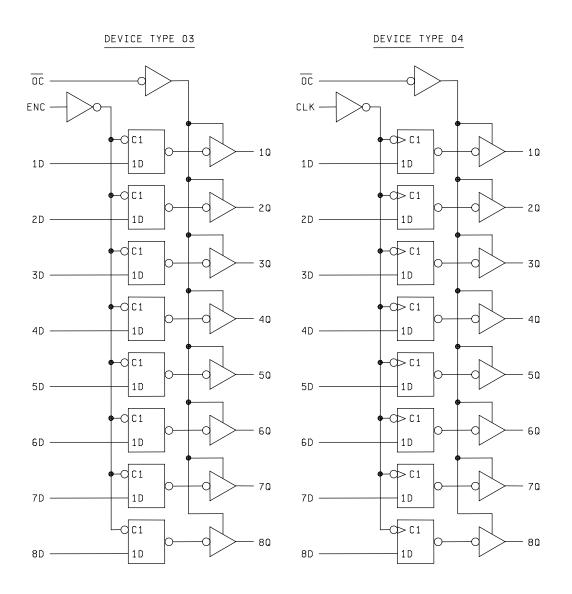


FIGURE 2. Logic diagrams - Continued.

Device type 01

		- 71	
	INPUTS	OUTPUT	
CLR	CLK	D	Q
L	Х	Х	L
Н	<b>↑</b>	Н	Н
Н	1	L	L
Н	L	Х	Q0

Device type 02

		71		
	INPUTS		OUT	PUT
CLR	CLK	D	Q	IØ
L	Х	Х	L	Н
Н	<b>↑</b>	Н	Н	L
Н	1	L	L	Н
Н	L	Х	Q0	Q <sub>0</sub>

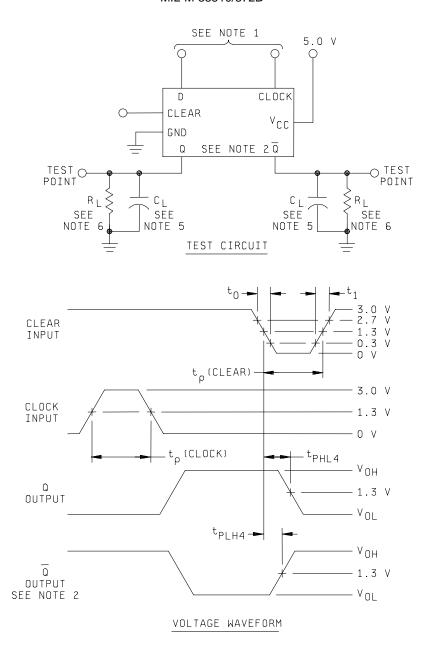
Device type 03

		7.	
	INPUTS		OUTPUT
OC	ENC	D	Q
L	Н	Н	Н
L	Н	L	L
L	L	Χ	Q0
Н	Χ	X	Z

Device type 04

	INPUTS		OUTPUT
OC	CLK	D	Q
L	<b>↑</b>	Н	Н
L	<b>↑</b>	L	L
L	L	Χ	Q0
Н	Χ	Χ	Z

FIGURE 3. <u>Truth tables.</u>



- 1. Clear input dominates regardless of the state of clock or D inputs.
- 2.  $\overline{Q}$  output applies to device type 02 only.
- 3. Clear input pulse characteristics:  $t_1 = t_0 = 6 \pm 1.5$  ns;  $t_{P(CLEAR)} = 15$  ns; PRR  $\leq 1.0$  MHz.
- 4. Inputs not under test are at ground.
- 5.  $C_L = 50 \text{ pF} \pm 10\%$ , including scope probe, wiring, and stray capacitance without package in test fixture.
- 6.  $R_L = 499\Omega \pm 1\%$ .
- 7. Clock input pulse characteristics:  $t_{P(CLK)} \ge 12.5$  ns, PRR  $\le 1.0$  MHz.
- 8. Voltage measurements are to be made with respect to network ground terminal.

FIGURE 4. A synchronous switching test circuit for device types 01 and 02.

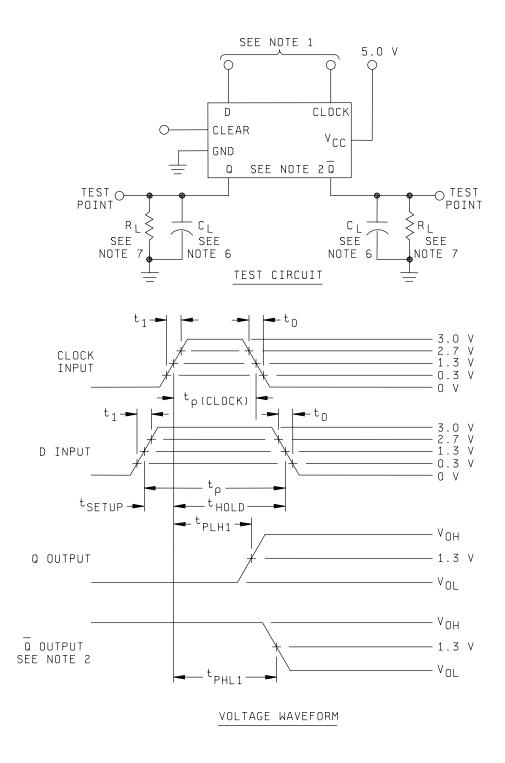
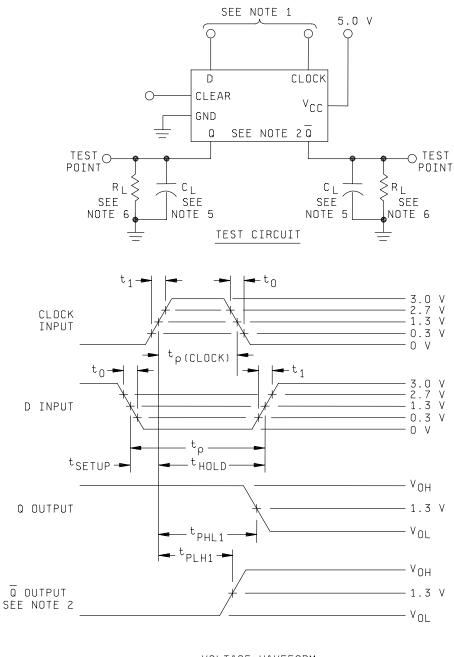


FIGURE 4. Synchronous switching test circuit (high-level data) types 01 and 02 - Continued.

## NOTES:

- 1. Clock input pulse characteristics:  $t_1 = t_0 = 6 \pm 1.5$  ns;  $t_{P(CLK)} = 12.5$  ns; PRR  $\leq 1.0$  MHz.
- 2. Q output applies to device type 02 only.
- 3. D input pulse characteristics:  $t_1 = t_0 = 6 \pm 1$  ns;  $t_{(SETUP)} = 15$  ns;  $t_{(HOLD)} = 0$  ns;  $t_P = 15$  ns; PRR is 50% of clock PRR.
- 4. For  $f_{MAX}$ , the clock input pulse characteristics are as follows:  $t_1 = t_0 \le 3$  ns; for 25°C,  $t_{P(CLK)} = 10$  ns; PRR = 50 MHz; for -55/125°C,  $t_{P(CLK)} = 12.5$  ns, PRR = 40 MHz. The D input pulse shall be one-half of the frequency of the clock and the D  $\uparrow$  and  $\downarrow$  shall be coincident with the clock  $\downarrow$ , but may be offset sufficiently to assure adequate  $t_{SETUP}$  and  $t_{HOLD}$  (see 1.4).  $t_1 = t_0 \le 3$ ns.
- 5. Inputs not under test are at ground.
- 6. C<sub>L</sub> = 50 pF ±10%, including scope probe, wiring, and stray capacitance without package in test fixture.
- 7.  $R_L = 499\Omega \pm 1\%$ .
- 8. Voltage measurements are to be made with respect to network ground terminal.

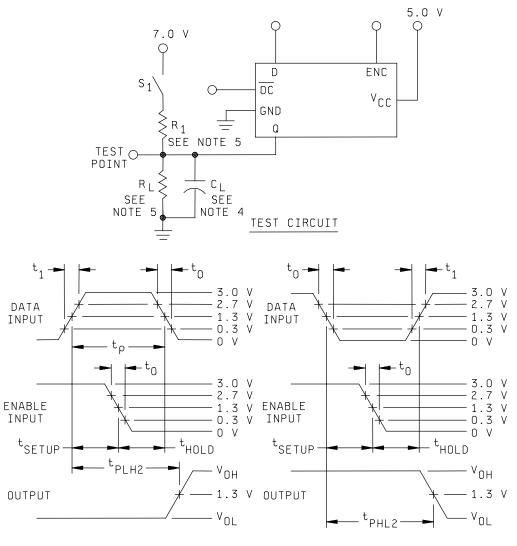
FIGURE 4. Synchronous switching test circuit (high-level data) types 01 and 02 - Continued.



# VOLTAGE WAVEFORM

- 1. Clock input pulse characteristics:  $t_1$  =  $t_0$  = 6 ±1.5 ns; PRR  $\leq$  1.0 MHz.
- 2.  $\overline{Q}$  output applies to device type 02 only.
- 3. D input pulse characteristics:  $t_1 = t_0 = 6 \pm 1.5$  ns;  $t_{(SETUP)} = 15$  ns;  $t_{(HOLD)} = 0$  ns; PRR is 50% of clock PRR.
- 4. Inputs not under test are at ground.
- 5. C<sub>L</sub> = 50 pF ±10%, including scope probe, wiring, and stray capacitance without package in test fixture.
- 6.  $R_L = 499\Omega \pm 1\%$ .
- 7. Voltage measurements are to be made with respect to network ground terminal.

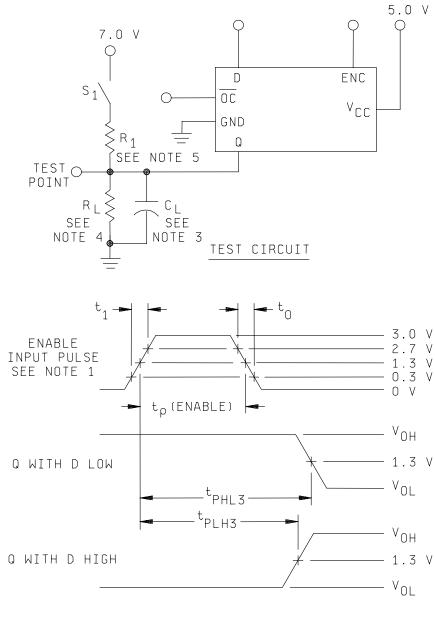
FIGURE 4. Synchronous switching test circuit (low-level data) types 01 and 02 - Continued.



VOLTAGE WAVEFORMS

- 1. Enable input pulse characteristics:  $t_0 = 6 \pm 1.5 \text{ ns}$ .
- 2. D input pulse characteristics:  $t_1 = t_0 = 6 \pm 1.5$  ns;  $t_{(SETUP)} = 10$  ns;  $t_{(HOLD)} = 7$  ns;  $t_P = 17$  ns.
- 3. Inputs not under test are at ground.
- 4. C<sub>L</sub> = 50 pF ±10%, including scope probe, wiring, and stray capacitance without package in test fixture.
- 5.  $R_L = R1 = 499\Omega \pm 1\%$ .
- 6. Voltage measurements are to be made with respect to network ground terminal.

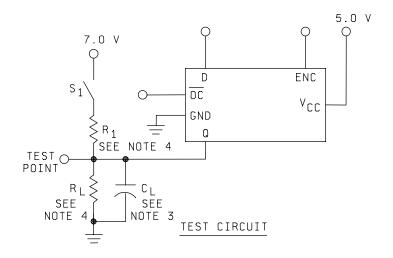
FIGURE 5. Switching time circuit, type 03.

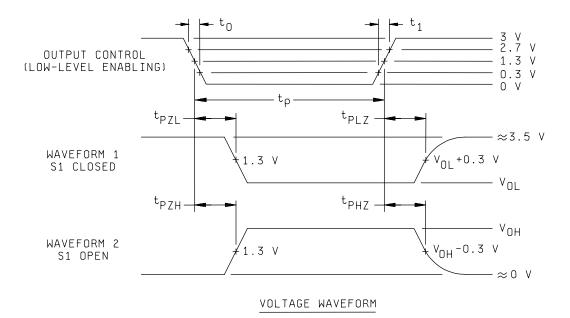


VOLTAGE WAVEFORMS

- 1. Enable input pulse characteristics:  $t_1 = t_0 = 6 \pm 1.5$  ns;  $t_P = 10$  ns; PRR  $\leq$  1 MHz.
- 2. Inputs not under test are at ground.
- 3.  $C_L = 50 \text{ pF} \pm 10\%$ , including scope probe, wiring, and stray capacitance without package in test fixture.
- 4.  $R_L = R1 = 499\Omega \pm 1\%$ .
- 5. Voltage measurements are to be made with respect to network ground terminal.

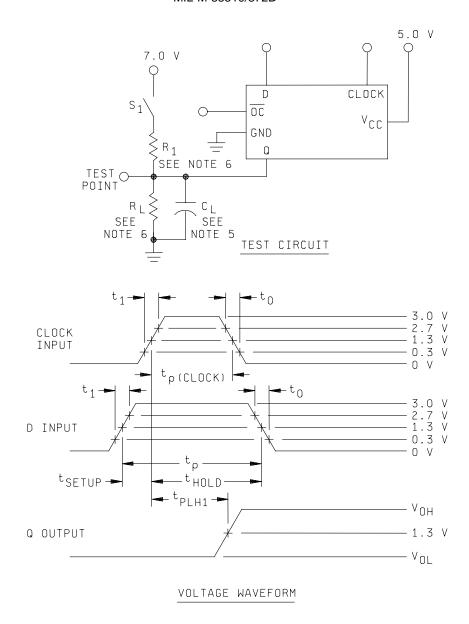
FIGURE 5. Switching test circuit, type 03 - Continued.





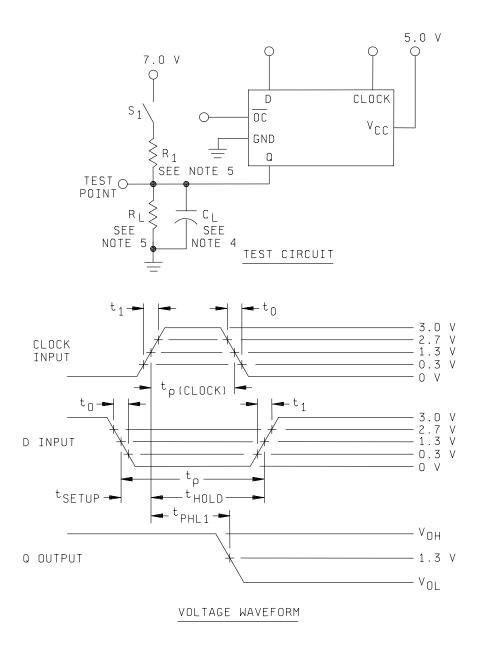
- 1. Output control input pulse characteristics:  $t_1 = t_0 = 6 = \pm 1.5$  ns;  $t_P = 200$  ns; PRR  $\leq 1$  MHz.
- 2. Inputs not under test are at ground.
- 3.  $C_L = 50 \text{ pF} \pm 10\%$ , including scope probe, wiring, and stray capacitance without package in test fixture.
- 4.  $R_L = R1 = 499\Omega \pm 1\%$ .
- 5. Voltage measurements are to be made with respect to network ground terminal.

FIGURE 5. Three-state switching test circuit, type 03 - Continued.



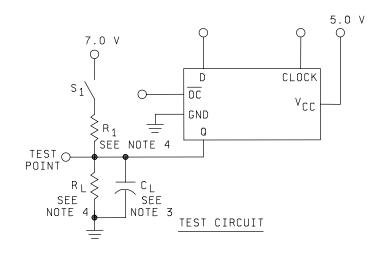
- 1. Clock input pulse characteristics:  $t_1$  =  $t_0$  = 6 ±1.5 ns;  $t_{P(CLK)}$  = 16.5 ns; PRR  $\leq$  1.0 MHz.
- 2. D input pulse characteristics:  $t_1 = t_0 = 6 \pm 1.5$  ns;  $t_{(SETUP)} = 10$  ns;  $t_{(HOLD)} = 4$  ns;  $t_P = 14$  ns; PRR is 50% of clock PRR.
- 3. For  $f_{MAX}$ , the clock input pulse characteristics are as follows:  $t_1 = t_0 \le 3$  ns; for 25°C,  $t_{P(CLK)} = 14$  ns; PRR = 35 MHz; for -55/125°C,  $t_{P(CLK)} = 16.5$  ns, PRR = 30 MHz. The D input pulse shall be one-half of the frequency of the clock and the D  $\uparrow$  and  $\downarrow$  shall be coincident with the clock  $\downarrow$ , but may be offset sufficiently to assure adequate  $t_{SETUP}$  and  $t_{HOLD}$  (see 1.4).  $t_1 = t_0 \le 3$ ns.
- 4. Inputs not under test are at ground.
- 5. C<sub>L</sub> = 50 pF ±10%, including scope probe, wiring, and stray capacitance without package in test fixture.
- 6.  $R_L = R_1 = 499\Omega \pm 1\%$ .
- 7. Voltage measurements are to be made with respect to network ground terminal.

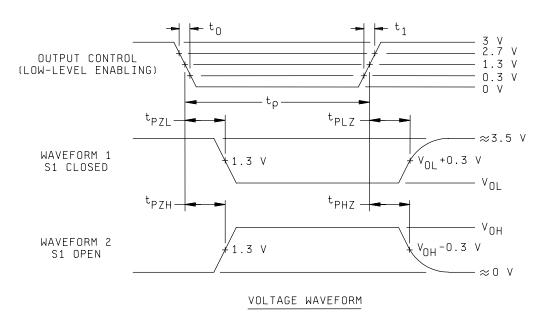
FIGURE 5. Synchronous switching test circuit (high level data) type 04.



- 1. Clock input pulse characteristics:  $t_1 = t_0 = 6 \pm 1.5$  ns;  $t_{P(CLK)} = 16.5$  ns; PRR  $\leq 1.0$  MHz.
- 2. D input pulse characteristics:  $t_1 = t_0 = 6 \pm 1.5$  ns;  $t_{(SETUP)} = 10$  ns;  $t_{(HOLD)} = 4$  ns;  $t_P = 14$  ns; PRR is 50% of clock PRR.
- 3. Inputs not under test are at ground.
- 4. C<sub>L</sub> = 50 pF ±10%, including scope probe, wiring, and stray capacitance without package in test fixture.
- 5.  $R_L = R_1 = 499\Omega \pm 1\%$ .
- 6. Voltage measurements are to be made with respect to network ground terminal.

FIGURE 5. Synchronous switching test circuit (low level data) type 04 - Continued.





- 1.  $\overline{OC}$  input pulse characteristics:  $t_1 = t_0 = 6 \pm 1.5$  ns;  $t_P \ge 200$  ns; PRR  $\le 1$  MHz.
- 2. Inputs not under test are at ground.
- 3. C<sub>L</sub> = 50 pF ±10%, including scope probe, wiring, and stray capacitance without package in test fixture.
- 4.  $R_L = R_1 = 499\Omega \pm 1\%$ .
- 5. Voltage measurements are to be made with respect to network ground terminal.

FIGURE 6. Three-state switching test circuit, type 04 - Continued.

TABLE III. Group A inspection for device type 01. Terminal conditions (pins not designated may be high  $\geq 2.0~\rm V$ ; low  $\leq 0.8~\rm V$ ; or open).

		Onit		>	-	=			-	=	-	=	=	=	=			=				: =		¥ĭ.	=		-	-	=	-			=	=			=	-			=	-		=	=	=		mA	=				
		ts	Мах							4.	=	=	=	=	-1.5			=		: =			·	ઝા								8	=		=			=	= 0	100	-	=	=	=	=			-112	=		: =	: =	
		Limits	Min	2.5	-	=																	Č	) ગ			-	-	-	-	=																	-20	=		: =	=	
		Measured terminal	•	1Q	20	30	40	05 50	a c	2 5	3 6	S &	Ž Č	09		í	2 6	70	25	Y Ç	40	20	GQ.	CLR	1D	2D	3D	CLK	4D	SD	Q9	CLR	1D	2D	3D	CLK	4D	5D	Q9	CLR	1D	2D	3D	CLK	4D	5D	6D	1Ω	20	gg ç	3 (	က္က တွ	
46	0	20	Vcc	4.5 V	-	-			=	=	=	-	-	=	=		-	=	-	: =			i	2.0					-	=	-	=	=					=			-	=	=	-	-			=	=				
16	2	19	<b>0</b> 9					V	-400 µA					4 mA																																					Ī	2.25 V	
. 7	4	18	О9					// // /	+					V 8.0								4	-18 mA								0.4 V								2.7 V						_		7.0 V			+	+	4.5 V	1
Terminal conditions (pins not designated may be high ≥ 2.0 V; low ≤ 0.8 V; or open).	2		2D					2.0 V	7				780	t							-	-18 mA	-							0.4 V	0							2.7 V	2							7.0 V	7		1	+	-	4.5 V	
0.8 V;							4	+					+	-								8L-								·. 0								2.							_	7.(			_	-	+		
low ≤ (	7	15	50					-400 μA					4 mA				-				7																												4	_	+	7.25 V	
2.0 V;	=	14	4D			_	2.0 V					0	0.0							40	/III & III-								0.4 \								2.7 V								7.0 V				Ц	,	4.5 V		
> high ≥	0	13	40				-400 µA					V w V	† = =																																						2.25 V		
may be	n.	12	CLK	2/	=	= :	= :	: :	=	=	=	=	=	=					4	-18 MA								0.4 V								2.7 V								7.0 V				2/	-	-	: =		
gnated	0	10	GND	GND	=	-			=	=	=	=		=	=		-	=	-													=	=					=			=	=	=	=				=	=		: =		
ot desi	,	6	30			-400 µA					V V	† [																																					<u> </u>	2.25 V	1		
(pins n	0	8	3D		7	2.0 \					// 0 0	+						10 20	¥ 0								0.4 V								2.7 V								7.0 /	 	_				$\dashv$	4.5 \	1	-	
ditions	n		2Q		-400 µA	``				/ w/	ł							Ì									_								•										_				2.25 V	+	_	-	
nal cor	4		2D		2.0 V -40					/ α ο	+						<	-18 mA								0.4 V								2.7 V								7.0 V		   	_				4.5 V 2.	+	+		
Term				2.0 V	2.				^	+	j					4	-18 mA	-								0.							^						-		7.0 V	7.			_			+	4	+	+	-	
									700	+				<u> </u>		,	-12	1	1	-					0.4 V								2.7 V						-		7.(							5 V 4.5 V	1	+	+	+	
c	7	3	10	ν -400 μΑ					4 20	4					٨		-		1					>								>								>					_			V 2.25 V	1	_	+	+	
L		2	CLR	2.0 V	=	=		: :	=	=	=	=	=	=	-18 mA		_							V.4.								2.7 \							1	7.0 \								4.5 V	1	_	4	_	
	E, F	Case 2 <u>1</u> /	Test no	1	2	က	4 -	2	7 0	- α	0 0	e (	2 5	12	13	,	4 7	C 4	10	1/0	Ω.	<u>6</u>	0.7	7	22	23	24	22	26	27	28	59	30	31	32	33	34	32	36	37	38	36	40	41	42	43	44	45	46	47	φ	50	
	MIL-STD-	883 method		3006	-				2002	200				-									0000	3008	=						-	3010							-									3011	=				
		Symbol		V <sub>он</sub>					>	NOL					Vıc								-	<u>=</u>								Ī							_  -	IH2								lo <u>4</u> ∕					
		Subgroup		1	To = 25°C																																																

See footnotes at end of table III.

TABLE III. Group A inspection for device type 01 - Continued.

Unit mA Max 19 Limits Min Measured terminal / Vcc 5.5 V 20 15 19 ВQ 4 GND 18 **Q9** Terminal conditions (pins not designated may be high  $\geq$  2.0 V; low  $\leq$  0.8 V; or open). GND 2D 15 5Q GND 14 4D 4Q 13 CLK 12 GND GND 10 30 3D 2Q 2D GND GND 1D Q CLR Test no. Cases E, F Case 2 1/ tests, termina MIL-STD-883 method 3005 Symbol Truth table tests °c = 25°C Subgroup 2

Terminals not referenced are N/C. 151

(pulse, prior to test). 2.0 V min/4.5 V max -- 0 V Apply

IL limits shall be as follows: %

		Min/Ma	Min/Max limits in µA for circuit	for circuit
Paran	Parameters	Α	В	0
ПI	D-inputs	0/-100		
	CLK/CLR	0/-150		

Method 3011 of MIL-STD-883 shall be used, except the output shall be as specified herein, and the output current shall be operating rather than short circuit current. Ios.

The output conditions have been chosen to produce a current that closely approximates one half of the true short circuit output current, Ios.

Tests shall be performed in sequence, attributes data only.

A = 2.4 V minimum, B = 0.4 V.

H > 1.5 V, L < 1.5 V. <del>4</del>।

 $f_{
m Max}$  minimum limit specified is the frequency of the input pulse. The output frequency shall be one-half of the input frequency. 181/1615

TABLE III. Group A inspection for device type 02. Terminal conditions (pins not designated may be high  $\geq$  2.0 V; low  $\leq$  0.8 V; or open).

									T						T	T											T				П	I	1			Ţ	T	П
	Unit		>	=	=	=	=		=	=	=	=	-			=	=	=	=	=		= =	=	=	=	=	-  -	=	μĄ	=	=	=	= =	=			: =	=
	its	Max												0.4		=	=	=	=	=	н		=	-1.5		=	=	=	/S		=	=	= =	20	=		: =	=
	Limits	Min	2.5	-					"		-	=	-																3/		=	=						
	Measured	<u> </u>	٦ ا	2 <u>Q</u>	301	4 Q	10	20 20	2 Q	ΙQ	2 0 0	ισ ε	4 Q	10	20 20 20	\$ Q	101	2 0	30	4 Q	10	20 20	8 04	CLR	1D	2D	SLK CLK	40	CLR	1D	2D	CLK	3D 4D	임	1D	2D	3D CE	4D
16	20	Vcc	4.5 V	-	=	=			=	=	-	=	-	=		=	=	=	-	=				=		=			5.5 V		=	=		=			: =	
15	19	Q 4							-400 µA							4 mA							4 mA															Ħ
4	18	Ισ				-400 µA			4-				-400 µA							4 mA																		П
open).		4 IQ				-400			>														>					۲					>					>
3 V; or	17	40							2.0 V				0.8 V							2.0 V			0.8 V					-18 mA					04.0	5				2.7 V
w ≤ 0.8	15	3D						^ 0	V.O.			0.8 V							2.0 V			\ 0 0	5				-18 m∆	2					0.4 \				2.7 V	
Terminal conditions (pins not designated may be high $\geq 2.0 \text{ V}$ ; low $\leq 0.8 \text{ V}$ ; or open).	14	30			-400 µA							-400 µA							4 mA																			
10 ≥ 2	13	ğ						4:: 004	400 HA						4	<u> </u>						48	<u> </u>															
ay be r	12	CLK					2/		-	=	=	=					2/	-	=	-	=						-18 mA					0.4 V				:	7.7.	
ated m	10	GND	GND						_	_	_	_				-		_	_	_				_		-	-		=			_		_				
design —			9					-400 μA							Ψ							Æ																
ins not	6	2Q		нΑ				-400			Αμ				4 mA			4				4 mA													H	-	-	
d) suo	8	20		-400 μA							-400 μA							4 mA																				
condit	7	2D						2.0 V			0.8 V							2.0 V				0.8 V									0.4 V					2.7 V		
erminal 4	2	9					2.0 V			0.8 V							2.0 V				0.8 V					-18 mA				0.4 V					2.7 V			
3 (6	4	10	-400 μΑ							-400 μA							4 mA								-18 mA													
2	3	10					-400 µA							4 mA							4 mA																	
-	2	SLR.	0.8 V	-	=	=	2.0 V	= =	=	=	=	=	=	0.8 V		=	2.0 V	=	-	=				-18 mA					0.4 V					2.7 V				
Cases	Case 2 1/	Test no.	-	2	3	4		9	8	6	10	11			14	16		18	19	20	21	22	24		26	27	28	30		32	33	34	35		38	39	40	42
			9						1																									-			<u> </u>	
E S			3006	-	=	=	-		=	=	-	=	-	3007		-	-	=	=	=	-		•						3009	-	-	-		3010	-			=
	Symbol		V <sub>он</sub>	0										$V_{OL}$										Vic					_=					<u>=</u>				_
	ubgroup		-	c = 25°C																																		

See footnotes at end of table III.

TABLE III. Group A inspection for device type 02 - Continued.

		Unit		γή		=			, Am	=			=	"	u	"	=										MHz	=		"	н	"	=		us			=	:		=	=
		Limits	Мах	100	=	=			-112	-	=	=	=				14																		14			=		-	=	=
		ij	Min						-20	)  -	=	=	=		=												50	=	-				=	=	က			=	:	=	=	=
		Measured terminal		<u>CLR</u>	1D	2D	CLK	3 4	4D	١٥	20 2	20	30	3 Q	40	4 Q	Vcc			12	ä						10	Ιά	20	2 <u>0</u>	30	3 Q	40	4 10	CLK to 1Q	CLK to 2Q	CLK to 3Q	CLN 10 4&	CLK to 1 a	CLK to $2\overline{\Box}$	CLK to 3 $\overline{\mathbb{Q}}$	CLK to 4 0 ☐
	16	20	οοΛ	5.5 V		=					"			"	"		=			4.5 V	=					-	5.0 V	=		н	н		=		= :			=	:		=	=
	12	19	40												2.25 V					ᆈ	= =	-	_:	Ι_	_	_							OUT				E	5				
(ر	4	18	4 Q													2.25 V				Ι-		ı	I	JI	I	I								OUT		1	+	$\dagger$				OUT
or oper	13	17	4D					;	7.0 /						4.5 V		GND			∢ <	ς α	<u>а</u>	⋖ -	∢ ∢	. ∢	V							Z	Z		1	2	2				Z
< 0.8 V;	12	15	3D				707	+					1.5 V	GND			GND			<b>4</b>	. α	<u>а</u>	A	<b>4</b> 4	. A	⋖					Z	Z				-	z	$\dagger$	_	_	Z	
Terminal conditions (pins not designated may be high $\geq 2.0$ V; low $\leq 0.8$ V; or open)		14	ΙØ				-							2.25 V (						<b>-</b>	, _	ı H	I	_ _ _		I						OUT				-		+			OUT	
th ≥ 2.0	0	13	3Q 3										2.25 V							_	- - -			T _		_					OUT	0				-	OUT	+				
y be hig	<u>ი</u>		CLK				7.0 /		/6	il=		_	2.3			_	_			B <	( a	1 4	В	< ¤	14	m	z				C		_	_	_			_	_		=	_
ated ma				<b>9</b>			7.			_	_	_								GND =	1						GND		L									$\frac{1}{1}$	$\dashv$			
designa			GND	GND		-	_	-					-		-		-	mitted.				ļ.				_	S			_	-					_		+		_	_	-
ins not			20						-		2.25 V	-						25°C and V <sub>LC</sub> tests are omitted	sts are om	_   1				Ι_		_			DOUT							OUT	+	+	$\dashv$	_		
tions (p	9	8	2 0			>					>	D 2.25 V					٥	and V <sub>IC</sub> t	ind V <sub>IC</sub> tes	Ι-				<b>-</b>	I	Η - (:	- - -			OUT					H	-	+	+		OUT		
al condi	Ω.		2D		H	7.0 V			>		4.5 V	GND					GND	= +125°C	= -55°C a	<b>4</b>	: a	α α	A		-	_	ုင် and -55°C 		Z	Z						Z	-	+		Z	_	
Termin	4	2	1D		7.0 V				4.5	N GND							GND	except T <sub>C</sub>	except T <sub>C</sub>	∢ <	( α	α α	Α :		=	=   .	I <sub>C</sub> = +125°C								Z		_	+	Z		_	
	က	4	10						,	2.25 V								group 1,	group 1,	Ι-	-	ı	I	<b>-</b>	I	Ξ,	7, except	TUO							H		+	Č	OUT			
	7	က	1Q						225 V	+-								its as suk	its as suk	_   _	=   I	-	_	Ι_	_	_	subgroup								OUT		_	+				
	-	2	CLR	7.0 V					457	=	=	=	=	-			GND	is, and lin	ıs, and lin	α <	ζ =	=	= :	= a	В	В	itions as a	=	-	=		=	=	=				=		=	=	=
	Cases E, F	Case 2 1/	Test no.	43	44	45	46	/4/	48	90	51	25	53	54	22	99	22	Same tests, terminal conditions, and limits as subgroup 1, except $T_{\rm C}$ = +1	Same tests, terminal conditions, and limits as subgroup 1, except $T_{\rm C}$ = -55°C and $V_{\rm IC}$ tests are omitted	28	309	61	62	63	92	99	Same tests and terminal conditions as subgroup 7, except 1 <sub>C</sub> f, 3003 67 3.0 V OUT	89	69	02	71	22	73	74	75	92	77	0/	6/	80	81	82
	MIL-STD-	883 method		3010	=	=			3011	- - - -	=	=		=	=	=	3005	sts, termina	sts, termina	3014	=	-	-				sts and terr 3003	(fig. 4)	-			=	=	-	= :			=		=	=	
		Symbol		I <sub>IH2</sub>					15.4/	i P							8	Same te:	Same te:	Truth	tests	Sisco					Same te	ર્જ જો							фгнл							
		Subgroup		1	$Tc = 25^{\circ}C$													2	3	7 7	0 - 20						ထ တ	2°C										_				

See footnotes at end of table III.

TABLE III. Group A inspection for device type 02 - Continued.

Unit Max Limits Min 9 8 2 CLK to 1Q CLK to 2Q CLK to 3Q CLK to 4Q CLR to 1Q CLR to 2Q CLR to 3Q CLR to 4Q Measured terminal CLR to 10 CLK to 2  $\overline{\mathbb{Q}}$ CLK to  $4\,\overline{\text{Q}}$ CLR to 2 Q CLR to 30 CLR to 4 Q CLK to 1 a CLK to 3 Q Vcc 20 OUT OUT 15 19 40 OUT OUT 14 18 1 Q Terminal conditions (pins not designated may be high  $\geq$  2.0 V; low  $\leq$  0.8 V; or open). 3.0 V 3.0 V 4D z z 3.0 V 15 3D Z 30 OUT OUT 4 OUT 30 13 CLK 12 7 GND GND 10 DOT 2Q OUT 2 Q  $\frac{1}{2}$ OUT Same tests and terminal conditions as for subgroup 9, except  $T_c = +125^{\circ}C$ . 3.0 V tests, terminal conditions and limits as for subgroup 10, except T<sub>C</sub> = -55°C. 3.0 V z 2D 3.0 V 10 Z OUT OUT Ιά Δ CLR Z Case 2 1/ Test no. Cases E, F 88 83 85 86 87 88 90 94 MIL-STD-883 method 3003 (fig. 4) Symbol fMAX 9 Tc = 25°C 10

Terminals not referenced are N/C.
Apply \_\_\_\_ 2.0 V min/4.5 V max Apply 151

(pulse, prior to test). > 0 -

3/ In limits shall be as follows:

		Min/Ma	Min/Max limits in µA for circuit	for circuit
Paran	Parameters	А	В	O
ᅦ	D-inputs	0/-100		
	CLK/CLR	0/-150		

Method 3011 of MIL-STD-883 shall be used, except the output shall be as specified herein, and the output current shall be operating rather than short circuit current. Ios.

The output conditions have been chosen to produce a current that closely approximates one half of the true short circuit output current, Ios.

Tests shall be performed in sequence, attributes data only. 4

A = 2.4 V minimum, B = 0.4 V. B > 1.5 V, L < 1.5 V. A > 1.5 V, A = 1.5 V.

In the frequency of the input pulse. The output frequency shall be one-half of the input frequency. 18 14 16 12

TABLE III. Group A inspection for device type 03. Terminal conditions (pins not designated may be high ≥ 2.0 V; low ≤ 0.8 V; or open).

Unit		>	-			=		-	-	-	Ī	=	-	=	=		-								-		-	-			=	μĄ					=	=		=	=		4	Y.		-	=	-	.  -	-		.  -	=			=	=	-	=			=	-	1
mits	Max										0.4	=		=	=	=	-			-1.5	-				=			=			-	1/			-	-	=	-	-	-	=	=	20	22		-	=	=		-			100	3	-	-	-	-	=	=	=	=	-	
Test limits	Min	2.4	-						=																							1/																	1															1
Measured	terminal	10	20	3Q	40	5Q	6Q	70	ί Q	S C	2	20	30	40	20	3 6	3 6	2 6	ğ	18	10	<u>.</u>	ZD SD	3D	40	ENC	בי	3	00	7D	8D	18	3 4	10	2D	3D	4D	ENC	2D	Q9	7D	8D	3	00	1D	2D	3D	4D	ENC	200	O I	0 6	3	00	10	2D	3D	4D	ENC	5D	6D	7D	. G	)
20 N	Vcc	4.5 V	-						=	-			=	=	=	=	-		.		-				=		=	=	1											=		=	55 \			-	=	=		-			-			=	=		=	=	-	=		1
19	80								-1 m	<u> </u>								4	12 MA																																		1											
18	8D								207	+								+	0.8 V												-18 mA											0.4 V										27.7	,										707	
17	7D							2.0 V	ŀ									v o.0												-18 mA	-,										0.4 V	-										2.7 \	1									7.0 V		-
16	۵۲ م							-1 mA	+								4	¥11 71												`.																							1											-
5 6 7 8 9 10 11 12 13 14 15 16	<b>0</b> 9						-1 mA	_								40.00	+	1																																														
41	Q9					_	2.0 V	-								, , , ,	+											10 20	Y I O											0.4 V										7.70	۰./ ۷		İ								7.0 /			-
13	5D					2.0 V	•								780	+											-18 mA	+											0.4 V	<u> </u>									21	+			-							7.0 V	-			1
12	20				-	-1 mA 2									12 m	+											-												0											7			-							_				1
11	ENC	2.0 V	=				"									-										-18 mA												0.4 V											2.7 V										7.0 V					1
10		GND							=	-		=	-	-		_	-		.		-					l- "	=	-								-		)		=	=	-					=	=					-		-	=	=	-	=		-	=	-	1
6	4Ω				-1 mA									12 mA																																							l											-
∞	4D			Н	2.0 V									V 8.0	t										-18 mA												0.4 V											2.7 V	1									7.0 V						1
7	3D			2.0 V									0.8 V											-18 mA												0.4 V											2.7 V										7.0 \							
9	30			-1 mA									12 mA																																																			
2	20		-1 mA									12 mA																																																				
	2D		2.0 V									0.8 V											-18 mA												0.4 V											2.7 V							L			7.0 \								
က	1D	2.0 V	-								۷.۵ ۷										-18 mA	2												0.4 V											2.7 V								ļ		7.0 V									- 5
2	Q Q	-1 mA								,	IZ MA					-				∢		_						-				,																	$\downarrow$															1:
-		0.8 V	-	-	=	=	=		=	-		=		=	=	=	-	-	-	-18 mA								-				0.4 V											277	, ,					$\downarrow$	-			7.0 V	2										1.0
Cases R, S, 2	Test no.	-	2	3	4	2	9	7	. α	0	מ	10	11	12	13	5 2	4	2 5	91	17	18	2 !	19	20	21	22	23	25	74	22	26	27	ć	528	29	30	31	32	33	34	32	36	37	õ	38	33	40	41	42	3	44	45	47	ř	48	49	20	51	52	53	54	25	56	Soc footpates of and of desired of
MIL-STD- 883	method	3006	=	=	=	=	=	=		0000	3007	=	=	=		=	=															3009			-	-	-	=	=	=	=	=	3010	2	=	-	=	=		=			=		=	=	=	=	=	=	=	=	-	40 004-
Subgroup Symbol		VoH								}	N <sub>OL</sub>									ر در												П											1	Ē									5	Ž H										1000
lbgroup	_	-	Tc = 25°C			_					-			_	-			_			_	_	_		-	_	_		-	_						_	-	_										_			_			_				_	_	_	_	_		Č

TABLE III. Group A inspection for device type 03. Terminal conditions (pins not designated may be high  $\geq 2.0~V$ ; low  $\leq 0.8~V$ ; or open).

Unit		<	¥.				.  -			=		-	-	-	-	=	=		ΜA	-		-		.			=	-	-												ns	-			=	-			-			-	-	=	-	=
	×	00	07-								20	-		-	_	=	=		-112	! =		=		.	-			16	25	27											12	=			=	=			16			-		=	-	-
Test limits	Min																		-20	╁																					2				=				4					=		_
red					1																																				1Q	2Q	30	4Q	5Q	9 0	7Q	80		2Q	30	40	5Q	90 80	۵۲ م	80
Measured	terminal	7	D G	77	OS (	4Q	g G	700	Ø.	8Q	1Q	20	DE 3O	40	20	09	02	80	CI	200	200	3 5	3 5	200	ტ9	ØZ	8 8	Λ	Vcc	Vcc					5/						1D to 1Q	2D to 2Q	3D to	4D to 4Q	5D to	6D to 6Q	7D to	8D to 8Q	1D to 1Q	2D to 2Q	3D to	4D to 4Q	5D to 5Q	6D to	7D to 7Q	8D to
20	Vcc	/ 4	2.5							=	-	=		=	=	=	=	=	=	=	=	=				=	=	=	=	=			4.5 V	=			=				5.0 V	=		=	=	=	=	-	=			=	-	=	=	=
19	80									0.4 V								2.7 V									2.25 V						I	_	٦	٦	I	I	I									DOL								D07
18	8D									2.0 V								0.8 \									4.5 V	4.5 V	GND	4.5 V			Α	В	В	٧	۷	Α	В									Z								Z
17	7D								2.0 V								0.8 V									4.5 V		4.5 V	GND	4.5 V			Α	В	В	٧	⋖	٧	В								Z								Z	
16	Δ							+	0.4 V								2.7 V	╄							_	2.25 V		`		•			н	7	٦	7	I	Н	I								OUT		H					_	OUT	_
15	09							0.4 V	0							277	t								2.25 V	2.							н	_	٦	7	I	I	I							OUT	0							OUT		
							+	+								H	-							+	-			>	D	>																										_
14	9				-		+	2.0 v							_	0.87								+	4.5 V			-		/ 4.5 V			A	В	В	A	٧	A	В							Z								Z		
13	5D					+	2.0 \								0.8 V	L							+	4.5 V				4.5 \	GND	4.5 V			Α	В	В	A	٧	Α	В						Z								Z	L		
12	2G						0.4 V								2.7 V									V CZ.Z									I	٦	٦	٦	I	н	I						OUT								OUT			
1	ENC																		45V	=	=	=	=			=	=	=	=				Α	۷	В	В	۷	В	В		Z	=	=	=	=	=	=	-	=			=		=	=	=
10	GND		GND							=		=		=		=	=		=	=	=	=		.			=	=	=				GND					н	н		GND	=		=	=	=						=		=		=
6	φ4					0.4 V								2.7 V								7 20 0	۷ ۲۰۶۰								omitted.	nitted.	I	7	٦	٦	I	н	I					OUT								OUT				
80	4D				:	2.0 V								V 8.0								7 2 /	_					4.5 V	GND	4.5 V	tests are omitted	ts are or	Α	В	В	A	∢	Α	В					Z								Z				
7	3D				2.0 V								V 8.0								45.7	>						4.5 V	GND	4.5 V	and V <sub>IC</sub> t	nd V <sub>IC</sub> tests are omitted	Α	В	В	Α	۷	Α	В	°C.			Z								Z					
9	30			+	V.4 V								2.7 V	╄							2 25 7	+									= +125°C a	55°C an	н	7	٦	7	I	I	I	and -55°C.			OUT								OUT					
2	20			0.4 V								2.7 V								2 25 \	_	7									$^{\circ}$ pt T $_{\rm C}$ = -	pt T <sub>c</sub> = -	Н	7	٦	7	I	I	I	= +125°C		OUT								OUT						
4	2D		-	2.0 V							-	0.8 V								457								4.5 V	GND	4.5 V	p 1, exce	p 1, exce	Α	В	В	Α	۷	Α	В	sept $T_{\rm C}$ =		Z							П	N						-
က	10	7.00	2.0 V								0.8 V								4 5 V	+							_	-		4.5 V	subgrou	subgrou	Α	В	В	A	4	Α	В	up 7, ex	z								Z							_
7	10	+	0.4 V								2.7 V								2 25 V	+											limits as subgroup 1, except T <sub>C</sub>	limits as	I	7	7	٦	I	н	I	s subgro	OUT								OUT							
-	18	3 6	2.0 V							=				=	=	=	=	-	CINE	t			2	OND.	=		=	=	=		ins, and	ins, and	В	=			=		н	ditions a	GND	=		=	=	=	=		=			=		=	=	=
Cases R. S. 2	Test no.	Ť	†	28	66	09	61	79	63	64	65	99	29	89	69	20	71	72	73	t	75	2,2	t	+	78	29	80	81		83	Same tests, terminal conditions, and	I conditio	84	85	tests " R B B L L	87	88	68	06	con		92	93	94	92	96	26	86	66	100	101	102	103	104	105	106
MIL-STD- C	method Te	1	_ _	_ _		_ _								1	<u> </u>		<u>L</u>	L	3011	 : -						_	=	3005	=	_	, termina	termina	214	_	_	_	_		_	and tern	3003	(fig. 5)					-	_	_	_	_	_	_		_	_
MIL	шe	+	고								Į,								+								1	-	7.	Z,	me tests,	me tests,	ith 30	e	ţ	4/			-	me tests		(fiç							77.							-
Subgroup Symbol	-	-	ZO	္							lozh								10.2/	•								l <sub>CCH</sub>	Iccr	lccz	Sai	Sai	Tr			8	]			Sai	<sup>‡</sup> РШ2	၁့င							t <sub>PHL2</sub>							-
Subaro	)	*	-	I c = 25°C																											2	က	7	Tc = 25°C						8	6	Tc = 25°C														

See footnotes at end of device type 03.

TABLE III. Group A inspection for device type 03. Terminal conditions (pins not designated may be high  $\geq 2.0~\rm V; low \leq 0.8~\rm V;$  or open).

	Unit		Su	=	=		=	=	=	н					=	=	=	=	-		=	=	=	=	=		=	=	=	=	=	=	=	=	=	=	=	=	-	=
	Test limits	Max	18	=	=	-  -	=	=		18			.		=	=	18	=	=	=	=	-	=	=	18	=	=	=	=	=	=	=	10	=	=	=	=	=	=	=
	Test	Min	9				=	=		7	= :				=	=	2			=	=	-	=	=	9	=		=	=	=		=	2					=	=	=
	Measured	terminal	ENC to 1Q	ENC to 2Q	ENC to 3Q	ENC to 4Q	FNC to 50	ENC to 7Q	ENC to 8Q	ENC to 1Q	ENC to 2Q	ENC to 30	ENC to 4Q	ENC to 50	ENC to 70	ENC to 8Q	OC to 1Q	0C to 2Q	OC to 3Q	OC to 4Q	0C to 5Q	0C to 6Q	0C to 7Q	OC to 8Q	0C to 1Q	0C to 2Q	OC to 3Q	OC to 4Q	<u>OC</u> to 5Q	00 to 60	OC to 70	0C to 8Q	0C to 1Q	0C to 2Q	OC to 3Q	<u>OC</u> to 4Q	0C to 5Q	<u>OC</u> to 6Q	<u>OC</u> to 7Q	OC to 8Q
20		Vcc	5.0 V	=	=		=	=		н					=	=		=		=	-	-	=	-	=	=	=	=	-	=		=	=	-		=		=	=	=
19		80							OUT							DUT								OUT								OUT								OUT
18	!	8D							3.0 V							GND								3.0 V								GND								3.0 V
17		7D						3.0 V							GND	!							3.0 V								GND								3.0 V	
open).	!	۷2						OUT							OUT								OUT								OUT								OUT	
8 V; or		09					TITO							F	5							OUT								OUT								OUT		
ow ≤ 0.8		О9					30.0							CIND	9							3.0 V								GND								3.0 V		
Terminal conditions (pins not designated may be high ≥ 2.0 V; low ≤ 0.8 V; or open)	!	2D				200	╁						4	GND							3.0 V								GND								3.0 V			
high ≥	ļ	50				E	+						+	100							) TUO								TUO								) TUO			
nay be		ENC	Z		=		=	=		н				: =	=																									
nated r	:	GND	GND				=	=							=	-	-	=	=	=	-	-	=	=	=	=	=	=	=	=	-	=	=	-	-	-	-		=	-
t desig		40	0			DOUT						!	100							TUO								OUT								OUT				
oins no		4D				3.0 V						_	GND							3.0 V								GND								3.0 V				
itions (r		3D			3.0 V						!	GND							3.0 V								GND								3.0 V					
al cond		30			OUT						!	DO T							OUT								TUO								OUT					
ermina 5		20		OUT							OUT							OUT								OUT								OUT						
_ 4		2D		3.0 V							GND							3.0 V								GND								3.0 V						
3		1D	3.0 V							GND							3.0 V								GND								3.0 V							
2	1	10	OUT							OUT							OUT								OUT								OUT							
-		18	GND				=	=							=	=	Z						-	=				=	=	=			=					=	=	=
Cases	R, S, 2	Test no.	107	108	109	110	112	113	114	115	116	117	118	179	121	122	123	124	125	126	127	128	129	130	131	132	133	134	135	136	137	138	139	140	141	142	143	144	145	146
IL-STD-	883	method	3003	(fig. 5)	=		=	=							=	-	-	-	=	-	-	-	=	=	=	-	-	=	-	-	-	-	=	-	-	-	-	-	=	=
2	ymbol		финз							t <sub>PHL3</sub>							фхн								t <sub>PZL</sub>								t <sub>PHZ</sub>							
	Subgroup Symbol		_	$Tc = 25^{\circ}C$																													l							

See footnotes at end of device type 03.

TABLE III. Group A inspection for device type 03.

ions (pins not designated may be high $\geq 2.0 \text{ V}$ ; low $\leq 0.8 \text{ V}$ ; or open)	13 14	9 Q5 (D)					d GND	GND											
ed may be hi	11 12	ENC 5Q					TUO												
designate	10	4Q GND	GND	=	=	T	=	=	=	=									
oins not o	8	4D 4(				GND OUT													
tions (p	2	3D			GND														
erminal condit	9	30			OUT								+125°C.						-1
rminal	2	20		OUT									ept TC =						om table
_ L	4	2D :		GND									9, exce						limits fro
	3	1D 2	9	O									apgroup						esn pu
			T GND										ns as su						-55°C a
	2	Δ Δ	TUO										condition						ept T <sub>C</sub> = ·
	s 1	9	Z	=	=	=	=	=	=	=			erminal						10, ехсе
	O- Cases R, S, 2	d Test no.	147	148	149	150	151	152	153	154			Same tests and terminal conditions as subgroup 9, except TC = +125°C.						Same tests as subgroup 10, except $T_{\text{c}}$ = -55°C and use limits from table
	MIL-STD- 883	method	3003	(fig. 5)	-	-	-	-	-	-			Same te						tests as s
	Symbol		t <sub>PLZ</sub>								t <sub>PLH2</sub>	t <sub>PHL2</sub>	tр⊔нз	t <sub>PHL3</sub>	tрzн	t <sub>PZL</sub>	t <sub>PHZ</sub>	t <sub>PLZ</sub>	Same
	Subgroup Symbol		6	$Tc = 25^{\circ}C$							10								11

1/ IL limits shall be as follows:

for circuit	S	
Min/Max limits in µA for circuit	В	
Min/Ma	Α	0/-200
	-Parameters	-    -

Wethod 3011 of MIL-STD-883 shall be used, except the output shall be as specified herein, and the output current shall be operating rather than short circuit current. Ios.
 The output conditions have been chosen to produce a current that closely approximates one half of the true short circuit output current, Ios.
 Tests shall be performed in sequence, attributes data only.
 A = 2.4 V and B = 0.4 V.
 V = 1.5 V, L = 1.5 V.

TABLE III. Group A inspection for device type 04. Terminal conditions (pins not designated may be high  $\geq 2.0~V;$  low  $\leq 0.8~V;$  or open).

Unit		>	=	=	.	.	.			.		.			.				-	=	=	=			-	=	-	-	μĄ			.	ŀ				=		-	Ą.			=		-	=			1			-	=	=	=	-	=	=	
nits	Max									9.4								-1.5	-	=	=	=							2/								=		-	20	=	=				=				100	-	-	=	=	=	-		н	
Test limits	Min	2.4	=																										2/																				1										
Measured	terminal	Ø	g	ğ	g	2 9	ğ	3 9	<u> </u>	3 9	g	g	ğ	g	g	3 9	ğ	18	_		3 5	2 5	Q .:	ŗĶ	Ω	Ω	70	Ω	15	2	ا ۵	Ö (	Š ;	Ot.	ب ک	Z i	ő	5 6	30	18	۵	Ω	3D	1D	ίĽΚ	Ω	3D	2 9	Ď	IS		ξ	2 0	Q.	붓	Θ	3D	7D	3D
						1	+			<u> </u>	4		7	4,	-					Ì		-	-		-,	•				_			1		1								.,						+	10									_
19 20	8Q V <sub>CC</sub>	4.5 V	-		-  -	<u> </u>			-1 mA	<u> </u>				-	<u>'</u>		12 mA	_	-	-	-	-				=		-	5.5 V					-		-	-			_	-	-			-	=	-		1	_	-	-	=	-	-	-	=		-
								_	_							7	7											μ											>									;	>										^
18	8D							$\dashv$	2.0 V						_	+	0.8 V										_	-18 mA										+	0.4 V									+	2.7 V										7.0 /
17	7D						_	2.0 V								۷ 8.0											-18 mA											0.4 V										2.7 V	1									7.0 V	
16	7Q						+	-1 mA							-+	12 mA																																	_										
8 9 10 11 12 13 14 15 16	09						-1 mA								12 mA																																												
41	Q9						2.0 V								0.8 \											-18 mA											0.4 V										2.7 V										7.0 V		
13	5D					2.0 V								0.8 \											-18 mA											0.4 V										2.7 V										7.0 V			
12	50				,	-1 mA								12 mA																																			1										
1	CLK	1/	=			.	: :	: :	: :					= :		: :								-18 mA										:	0.4 V										2.7 V				†						7.0 V				
10	GND	GND	=			.				.		.			.			-				-	T	-								.		1			=												_	_			=			_			
6	40	0			-1 mA								12 mA																																				1										
80	4D			Н	2.0 V							-	0.8 V									40 04	8 IIA											0.4 V										2.7 V					1					7.0 V					
	3D			2.0 V								0.8 V									10 m	_	-										0.4 v										2.7 V						1				7.0 V	٠					
5 6 7	30			-1 mA								12 mA									_	-																											_				-						
2	20		-1 mA	,-							12 mA	-																																					1										
4	2D		2.0 V								0.8 V									10 20	<u>ا</u>											0.4 V										2.7 V							+			707							
ဇ	1D	2.0 V								0.8 \									-18 mA												0.4 V										2.7 V								1		7.0.7	+							
2	10	-1 mA								12 mA									ľ																														1										
-	18	0.8 \	=	=	-	.				.		.			.			-18 mA	l										0.4 V											2.7 \									30	7.0.7		l							
Cases R, S, 2	Test no.	1	2	3	4 -	2	9 1	,	∞ (	ກ :	10	11	12	13	14	15			18	2 0	8 6	0 2	1.7	22	23	24	25	56	27		28	29	ος 1	31	32	33	34	35	36	37	38	39	40	41	42	43	44	45	40	47	48	49	50	51	52	53	54	22	" 56
MIL-STD- 6 883 F	method	3006	-							3007												_1_					<u> </u>		3009								l		-	3010	=	-	-	-	-	=	_		+			-	-	-		-	-	-	
MII.		V <sub>OH</sub>							+	V <sub>OL</sub>								o N											3										+	H									+	IH2									
Subgroup Symbol		>							-	>								>																					ľ	_										_									
Subgr		-	Tc = 25°C																																																								

TABLE III. Group A inspection for device type 04. Terminal conditions (pins not designated may be high  $\geq$  2.0 V; low  $\leq$  0.8 V; or open).

Unit		μA						"	"		=		=		=		=	mA										-										MHz			.				Su	2 =	=	-	=	=	=	=
nits	Max	-20		=	-					20			=	=	=	=	=	-112								6	28	31																	12	<u>1</u> =	-					
Test limits	Min																	-50																			•	35							4	r =	=	=	-	=		=
Measured	terminal	10	20	30	40	5Q	6Q	7Q	8Q	1Q	20	30	4Q	5Q	09	70 2	8Q	1۵	20	) )	40	20	Ø :	Ŋ (	ж Э	8,	200	Voc				//	i				-	1۵	20	30	40 0	200	) (1)	2 0	CI K to 10	OLK 15 20	CLK 10 20	CLR to 40	CLK to 5Q	CLK to 6Q	CLK to 7Q	CLK to 8Q
20	Vcc	5.5 V		-	=		=						-	-	-	-	-	-			-			.				=		7 2 7	v C.+		=		-			5.0 V			.				-		-	=		=		=
19	80								0.4 V								2.7 V							,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	7.25 V					/3 /	ÒI I	Ξ	Ξ	:   _	٦	Ι								F	5							OUT
18	8D								2.0 V								0.8 V							,	V.5.V	V C.4	GND	GND		<	۷ ۵	( B	В	<u>а</u>	4	٨								Z	2	Ì						z
17	70							2.0 V								0.8 V							;	4.5 V		V C.4	GND	GND		<	۷ ۵	В	В	<u>а</u>	4	٧	•							Z		Ī					Z	_
16	70							0.4 V								2.7 V								7.25 V						/3 /	ĵ! I	Ξ	I	:  -	_	т							ŀ	100		1	1	1	-		OUT	_
15	09						0.4 V								2.7 V								2.25 V							/3 ^	òl I	ī	I	:   _	7	I	•					Ē	100					-		OUT		_
41	Q9						2.0 V								0.8 V							+	4.5 \			V C.4	GND	GND		<	۷ ۵	( B	В	<u>а</u>	⋖	Α						2	z			+	+		ŀ	Z		_
13 14	2D					2.0 V								0.8 V								4.5 V			+	V C.4	+	-		<	۲ ۵	( m	В	ω ω	4	Α	•				-	Z				+	+	+	Z			_
12	50					0.4 V								2.7 V								2.25 V								/3 ^	òl I	   	ī	:  -	_	I					Ŀ	5				+	t	+	DUT			_
7 8 9 10 11	CLK	1/		=								н	=	=	=		=							.						٥	۵ ۵	< <	В	<b>1</b> <	В	A	•	Z							=	=	=	=	=	=	=	=
10	GND	GND		=		-		"	"					=	=	=	=							.		-		=		CINO	ם וויי	=			=	-	•	GND							=	-	=	=	-	=		=
6	40				0.4 V								2.7 V								2.25 V							140.00	ornitted.	ŀ	Ò I	: =	-	_	_	I	•			!	5					T	T	TUO				_
8	4D				2.0 V								0.8 V							_	4.5 V				,	V C.4	GND	GND	tests are ornitted	is ale of	۷ ۵	В	=		4	Α	•			1	Z					Ī		z	:			
	3D			2.0 V								0.8 V								4.5 V						V C.4	GND	GND	and V <sub>IC</sub> tests are offlitte	sal oly bi	۷ ۵	: В	=		A	٧	55°C.			z						Ī	Z	2				
	30			0.4 V								2.7 V								7.25 V									-+123-0	-35 Ca   × e/	Ò I	: =	=	7	٦	Ŧ	C and -5		į	OUT						Ī	Ē	3				
5 6	20		0.4 V								2.7 V								2.25 V									T +	ept Ic	- older	) I			٦	٦	Н	= +125°		OUT							OIIT	3					
4	2D		2.0 V								0.8 V								4.5 V						, , ,	4.5 V	GND	GND	up I, ex	nb ı, ex	۲	В	=		A	Α	xcept T <sub>c</sub>		Z							N	=					
3	10	2.0 V								0.8 V								4.5 V							,	V C.4	GIND GIND	GND	orbans	oigans ,	۷ ۵	В	=		٧	٧	oup 7, e	Z							Z	<u>:</u>						
2	D1	0.4 V								2.7 V								2.25 V										land the	limits at		Ò I	: -	=	_	٦	I	าร subgr	OUT							Lic	3	T	Ī	Ī			
-	18	2.0 V		=			=						=	=	=			GND				GND				-		4.5 V	ons, and	olis, allu	- ۵	-	=	=	=	-	ditions a	GND							-	-	-	=	-	-	=	=
Cases R, S, 2	Test no.	22	58	29	90	61	62	63	64	65	99	29	89	69	20	71	72	73	74	(2)	9/	11	78	£ 5	080	<u>0</u>	82	83	al condition	al Collula	85.	86	87	88	68	06	minal cor.		92	93	94	င္သ	36	/6	000	3 5	3 5	102	103	104	105	106
MIL-STD- 883	. poutau							لــــا			,							3011								cons		= 04	Some tests, terrifical conditions, and limits as subgroup 1, except $1_C = +1.25^{\circ}C$	2017	110til 3014 04 B \\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	-	=	-	=	=	Same tests and terminal conditions as subgroup 7, except $T_{\text{C}}$ = +125°C and	3003	(fig. 6)						=	-	-	-	-	-	=	=
N lodm,		lozr								lоzн								_ ଜୁ								CCH	LCCL	ccz	Same tex	Same lex	num	ests	4/ 5/	ο i			same tes	fMAX							ţ	- FH-1						1
Subgroup Symbol		-	rc = 25°C																						-1	_1_			7 6	Ī	Tr = 25°C +		-						Tc = 25°C						<u>1</u>							

See footnotes at end of device type 04.

TABLE III. Group A inspection for device type 04. Terminal conditions (pins not designated may be high  $\geq$  2.0 V; low  $\leq$  0.8 V; or open).

	Unit		ns				-				-		=								-												-	=
	mits	Max	16			н				=	17	-	=	=		=	=		18			=			=		10	=			-		=	=
	Test limits	Min	2			н					က		=	=					2			=			=	=	-						-	=
	Measured	terminal	CLK to 1Q	CLK to 2Q	CLK to 3Q	CLK to 4Q	CLK to 5Q	CLK to 6Q	JLK to /Q	CLK to 8Q	OC to 1Q	<u>oc</u> to 20	OC to 3Q	OC to 4Q	OC to 5Q	0C to 6Q	OC to 70	0C to 8Q	OC to 1Q	<u>oc</u> to 20	OC to 3Q	OC to 4Q	OC to 5Q	0C to 6Q	OC to 7Q	OC to 8Q	0C to 1Q	<u>0C</u> to 2Q	OC to 30	OC to 4Q	OC to 5Q	<u>OC</u> to 6Q	OC to 7Q	OC to 8Q
00		Vcc	5.0 V		"	)							=	-		=				-	=		=			=		=	=				-	=
10	2	80								OUT								OUT								OUT								OUT
18	2	8D								Z								3.0 V								GND								3.0 V
17	<u>-</u>	7D						-	2								3.0 V								GND								3.0 V	
or open).	2	7Q						Ŀ	100								) TUO								OUT								OUT :	
5 V; Or C	2	09						OUT								OUT								DUT								OUT		
W ≤ U.2	<u> </u>	О9						Z								3.0 V								GND								3.0 V		
2.0 V; IC	2	2D					Z								3.0 V	(6)							GND								3.0 V	3		
(pins not designated may be nign ≥ 2.0 v; low ≤ 0.8 v;		50					OUT								OUT 3								OUT								OUT 3			
nay be r		CLK :	z				J			=	<del>-</del>	-	=	=	5	=	-	=	=	-		-	- -	=	=	=	=	=	=	=			-	-
nated m		GND	GND							-	-		=	=		=			=				=		=		=	=	=				-	=
design		4Q G	G			OUT								OUT								OUT								OUT				
ins not	0	4D				N								3.0 V								GND								3.0 V				
	,	3D			Z								3.0 V	(,)							GND	)							3.0 V	(6)				
condit	0	30			OUT								) TUO								OUT								) TUO					
erminal conditions	0	20		OUT								OUT								OUT								OUT						
4	+	2D		Z								3.0 V								GND								3.0 V						
۲	,	1D	Z								3.0 \								GND								3.0 V							
٥	7	1Q	DOUT								OUT								OUT								OUT							
-		18	GND	и	=	н				=	Z	-	=	=		=		=	=	-	=	=	=	=	=	=	=	=	=	=	-	=	-	
Case	R, S, 2	Test no.	107	108	109	110	111	112	113	114	115	116	117	118	119	120	121	122	123	124	125	126	127	128	129	130	131	132	133	134	135	136	137	138
-STD-		method	3003	(fig. 6)	=		-			=		-			-			-	=		=	-	-	-	-		=		-	-				-
	lodmy		t <sub>PHL1</sub>								фдн								t <sub>PZL</sub>								t <sub>PHZ</sub>							
	Subgroup Symbol		6	$Tc = 25^{\circ}C$						_1									I								I .							

See footnotes at end of device type 04.

TABLE III. Group A inspection for device type 04.

	Ħ		s	L	L	l_	İ_		Ĺ	Ĺ	۲ <sub></sub>	'n			<u>.                                    </u>	L	L	
	Unit		ns	-	=	=	=	-	-	-	MHz	ns	=	-	-	-		
	Test limits	Max	18	=	=	=	=		=	=		20	18	22	20	12	24	
	Tes	Min	2	=	=	=	=	-	=	=	30	4	2	2	7	2	3	
	Measured	terminal	OC to 1Q	0C to 2Q	OC to 3Q	OC to 4Q	0C to 5Q	09 ot <u>20</u>	OC to 7Q	0C to 8Q								
	20	Vcc	5.0 v	=	=	=	=	-	=	=								
	19	80								OUT								
	18	8D								GND								
	17	ZD							GND									
r open)	16	7Q							OUT									
.8 V; o	15	90						OUT										
$low \le 0$	14	Q9						GND										
Terminal conditions (pins not designated may be high $\geq 2.0 \text{ V}$ ; low $\leq 0.8 \text{ V}$ ; or open)	13	2D					GND											
e high ≥	12	2Q					TUO											
may b	11	CLK	1/	=	=	=	=		=	=								
ignated	10	GND	GND	=	=	=	=	=	=	=								
ot des	6	40				OUT												
pins n	8	4D				GND												
litions (	7	3D			GND									ci				
ial cond	9	30			OUT									) = +125°(				ple I.
Termir	2	2Q		OUT										cept TC				from ta
	4	2D		GND										onb 9, e				use limit
	3	10	GND											as subgr	)			5°C and ∣
	2	Q1	OUT											nditions				T <sub>c</sub> = -5
	1	18	Z	=	=	=	=		=	=				minal co				, except
	Cases R, S, 2	Test no.	139	140	141	142	143	144	145	146				Same tests and terminal conditions as subgroup 9, except TC = +125°C.				Same tests as subgroup 10, except $T_{\rm c}$ = -55°C and use limits from table I
	MIL-STD- 883	method	3003	(fig. 6)	=	=	=	-	-	=				Same tes				ests as su
			t <sub>PLZ</sub>								f <sub>MAX</sub>	t <sub>PLH1</sub>	t <sub>PHL1</sub>	tрZн		t <sub>PHZ</sub>	t <sub>PLZ</sub>	Same t
	Subgroup Symbol		o	Tc = 25°C							10				•			11

(pulse, prior to test). 2.0 V min/4.5 V max -- 0 V  $\frac{1}{4}$  Apply

2/ IL limits shall be as follows:

	Min/Ma	Min/Max limits in µA for circuit	for circuit
Parameters	А	В	Э
	0/-500		

3/ Method 3011 of MIL-STD-883 shall be used, except the output shall be as specified herein, and the output current shall be operating rather than short circuit current. In the output conditions have been chosen to produce a current that closely approximates one half of the true short circuit output current, Ios.
 4/ Tests shall be performed in sequence, attributes data only.
 5/ A = 2.4 V, minimum, B = 0.4 V.
 6/ X = indeterminate output voltage.
 1/ H > 1.5 V, L < 1.5 V.</li>

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f<sub>MAX</sub> minimum limit specified is the frequency of the input pulse. The output frequency shall be one-half of the input frequency.

## 5. PACKAGING

5.1 <u>Packaging requirements.</u> For acquisition purposes, the packaging requirements shall be as specified in the contract or order (see 6.2). When actual packaging of materiel is to be performed by DoD or in-house contractor personnel, these personnel need to contact the responsible packaging activity to ascertain packaging requirements. Packaging requirements are maintained by the Inventory Control Point's packaging activity within the Military Service or Defense Agency, or within the military service's system command. Packaging data retrieval is available from the managing Military Department's or Defense Agency's automated packaging files, CD-ROM products, or by contacting the responsible packaging activity.

## 6. NOTES

- 6.1 <u>Intended use.</u> Microcircuits conforming to this specification are intended for original equipment design applications and logistic support of existing equipment.
  - 6.2 Acquisition requirements. Acquisition documents should specify the following:
    - a. Title, number, and date of the specification.
    - b. PIN and compliance identifier, if applicable (see 1.2).
    - c. Requirements for delivery of one copy of the conformance inspection data pertinent to the device inspection lot to be supplied with each shipment by the device manufacturer, if applicable.
    - d. Requirements for certificate of compliance, if applicable.
    - e. Requirements for notification of change of product or process to contracting activity in addition to notification to the qualifying activity, if applicable.
    - f. Requirements for failure analysis (including required test condition of method 5003 of MIL-STD-883), corrective action, and reporting of results, if applicable.
    - g. Requirements for product assurance options.
    - h. Requirements for special carriers, lead lengths, or lead forming, if applicable. These requirements should not affect the part number. Unless otherwise specified, these requirements will not apply to direct purchase by or direct shipment to the Government.
    - i. Requirements for "JAN" marking.
    - j. Packaging requirements (see 5.1).
- 6.3 <u>Superseding information</u>. The requirements of MIL-M-38510 have been superseded to take advantage of the available Qualified Manufacturer Listing (QML) system provided by MIL-PRF-38535. Previous references to MIL-M-38510 in this document have been replaced by appropriate references to MIL-PRF-38535. All technical requirements now consist of this specification and MIL-PRF-38535. The MIL-M-38510 specification sheet number and PIN have been retained to avoid adversely impacting existing government logistics systems and contractor's parts lists.
- 6.4 <u>Qualification</u>. With respect to products requiring qualification, awards will be made only for products which are, at the time of award of contract, qualified for inclusion in Qualified Manufacturers List QML-38535 whether or not such products have actually been so listed by that date. The attention of the contractors is called to these requirements, and manufacturers are urged to arrange to have the products that they propose to offer to the Federal Government tested for qualification in order that they may be eligible to be awarded contracts or purchase orders for the products covered by this specification. Information pertaining to qualification of products may be obtained from DSCC-VQ, 3990 E. Broad Street, Columbus, Ohio 43123-1199.

6.5 <u>Abbreviations, symbols, and definitions</u>. The abbreviations, symbols, and definitions used herein are defined in MIL-PRF-38535, MIL-HDBK-1331, and as follows:

GND	Ground zero voltage potential
I <sub>IN</sub>	Current flowing into an input terminal

- 6.6 <u>Logistic support.</u> Lead materials and finishes (see 3.4) are interchangeable. Unless otherwise specified, microcircuits acquired for Government logistic support will be acquired to device class B (see 1.2.2), lead material and finish A (see 3.4). Longer length leads and lead forming should not affect the part number.
- 6.7 <u>Substitutability.</u> The cross-reference information below is presented for the convenience of users. Microcircuits covered by this specification will functionally replace the listed generic-industry type. Generic-industry microcircuit types may not have equivalent operational performance characteristics across military temperature ranges or reliability factors equivalent to MIL-M-35810 device types and may have slight physical variations in relation to case size. The presence of this information should not be deemed as permitting substitution of generic-industry types for MIL-M-38510 types or as a waiver of any of the provisions of MIL-PRF-38535.

Military device type	Generic-industry type
01	54ALS174
02	54ALS175
03	54ALS373
04	54ALS374

6.8 <u>Manufacturers' designation.</u> Manufacturers' circuits which form a part of this specification are designated with an "X" as shown in table IV herein.

TABLE IV. Manufacturers' designations.

		Circ	uits
Device	Α	В	С
type	Texas	Motorola Inc.	National Semiconductor/
	Instruments		Fairchild Semiconductor
01	X		
02	X		
03	X		
04	Х		

6.9 <u>Changes from previous issue.</u> Marginal notations are not used in this revision to identify changes with respect to the previous issue due to the extensiveness of the changes.

Custodians: Preparing activity:
Army - CR DLA - CC

Army - CR Navy - EC Air Force - 11

Air Force - 11 (Project 5962-2054) DLA - CC

Review activities:

Army - MI, SM Navy - AS, CG, MC, SH, TD Air Force - 03, 19, 99

NOTE: The activities listed above were interested in this document as of the date of this document. Since organizations and responsibilities can change, you should verify the currency of the information above using the ASSIST Online database at <a href="https://www.dodssp.daps.mil">www.dodssp.daps.mil</a>.